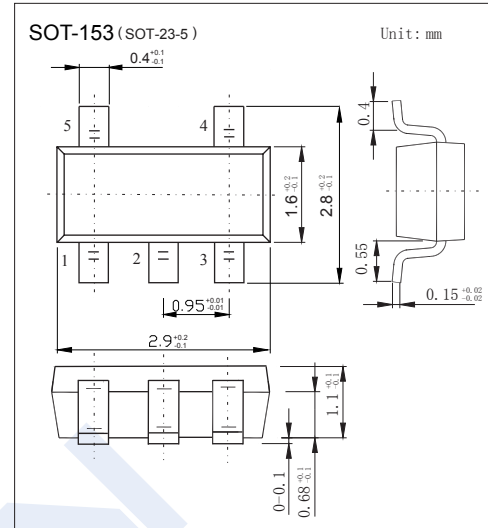
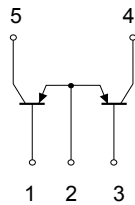


PNP Transistors

FMS3 (KMS3)

■ Features

- Collector Current Capability $I_c = -50\text{mA}$
- Collector Emitter Voltage $V_{CE0} = -120\text{V}$
- High breakdown voltage.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-120	V
Collector - Emitter Voltage	V_{CE0}	-120	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_c	-50	mA
Collector Power Dissipation	P_c	300	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_c = -100 \mu\text{A}$, $I_E = 0$	-120			V
Collector- emitter breakdown voltage	V_{CE0}	$I_c = -1 \text{mA}$, $I_B = 0$	-120			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}$, $I_c = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -100 \text{V}$, $I_E = 0$			-0.5	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -4\text{V}$, $I_c = 0$			-0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -10 \text{mA}$, $I_B = -1\text{mA}$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = -10 \text{mA}$, $I_B = -1\text{mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -6\text{V}$, $I_c = -2\text{mA}$	180		820	
Transition frequency	f_T	$V_{CE} = -12\text{V}$, $I_E = 2\text{mA}$, $f = 100\text{MHz}$		140		MHz

■ Marking

Marking	S3
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